CLAIM AMENDMENTS

1 - 10. (canceled)

11. (currently amended) The method according to claim 22, further comprising the step of ~~1 characterized by the choice of~~ using selenium, sulfur or tellurium as the chalcogen.

12. (currently amended) The method according to claim 22 wherein ~~1 characterized in that~~ the passivation element is implanted with a dose of 10^{12} to 10^{16} cm^{-2}~~, especially 10^{14} to 10^{15} cm^{-2}~~.

13. (currently amended) The method according to claim 22, further comprisign the step of ~~1 characterized in that the~~ selecting metal component of the metal silicide or metal germanide ~~is selected~~ from the group of cobalt, nickel, titanium, tungsten [[and/]]or molybdenum.

14. (currently amended) The method according to claim 22 wherein ~~1 characterized in that~~ the silicon component of the silicide as the ~~first layer~~ metal silicide is comprised of polysilicon or amorphous silicon.

15. (canceled)

16. (currently amended) The method according to claim 22, further comprisign the step of ~~1 characterized in that~~ providing a mask ~~is arranged~~ on the adjoining layer.

17. (currently amended) An electronic component comprised of at least one passivated metal-semiconductor or metal-insulator contact made in accordance with claim 22 [[1]].

18. (currently amended) A Schottky barrier MOSFET with an adjustable, especially negative Schottky barrier as the source [[and/]] or drain contact of an electronic component according to claim 17.

19. (currently amended) A Schottky barrier MOSFET according to claim 18 ~~characterized in that~~ wherein the contact has a silicon thickness smaller than 30 nm ~~arranged~~ on an ultra thin SOI substrate.

20. (currently amended) A MOSFET with a gate contact adjusted by means of passivation as an electronic component according to claim 17.

21. (currently amended) A spin transistor as the electronic component according to claim 17 ~~characterized in that~~ wherein a semiconductor silicide is selected as the ~~first layer~~

metal silicide with Mn or Fe or Co doping for the formation of magnetic source and drain contacts.

22. (new) A method of making a contact between a first layer comprised of a metal silicide or metal germanide and a substrate adjacent the first layer and including silicon or germanium, the method comprising the steps of:

a) incorporating by ion implantation close to a surface of the substrate or depositing on the surface of the substrate chalcogen as a passivation element;

b) depositing on the substrate or on the chalcogen a metal component of the first layer to create a structure; and

c) thermally treating the structure to form by solid-state reaction the first layer while simultaneously enriching the chalcogen by segregation at least at an interface between the first layer and the substrate to produce the contact.

23. (new) The method defined in claim 22 wherein the substrate includes Si-Ge-C, Si-C, or Si-Ge.

24. (new) A method of making a contact between a first layer comprised of a metal silicide, metal germanide, or semiconductor silicide and a substrate adjacent the first layer and including silicon or germanium, the method comprising the steps of:

a) depositing on a surface of the substrate a metal component of the first layer;

b) incorporating by ion implantation close to the surface of the substrate chalcogen as a passivation element to create a structure; and

c) thermally treating the structure to form by solid-state reaction the first layer while simultaneously enriching the chalcogen by segregation at least at an interface between the first layer and the substrate to produce the contact.

25. (new) The method defined in claim 24 wherein step a) precedes step b).

26. (new) The method defined in claim 24 wherein step b) precedes step a).

27. (new) The method defined in claim 24 wherein the chalcogen is incorporated in the substrate close to the surface.

28. (new) The method defined in claim 24 wherein the chalcogen is incorporated in the metal component close to the surface.

29. (new) The method according to claim 24, further comprising the step of

using selenium, sulfur or tellurium as the chalcogen.

30. (new) The method according to claim 24 wherein the passivation element is implanted with a dose of 10^{12} to 10^{16} cm^{-2}.

31. (new) The method according to claim 24, further comprising the step of

selecting metal component of the metal silicide or metal germanide from the group of cobalt, nickel, titanium, tungsten or molybdenum.

32. (new) The method according to claim 24 wherein the silicon component of the silicide as the metal silicide is comprised of polysilicon or amorphous silicon.

33. (new) The method according to claim 24, further comprising the step of

using β-$FeSi_2$, Ru_2Si_3, $MnSi_x$ or $CrSi_2$ as a semiconductor silicide.

34. (new) The method according to claim 24, further comprising the step of

providing a mask on the adjoining layer.

35. (new) An electronic component comprised of at least one passivated metal-semiconductor or metal-insulator contact made in accordance with claim 24.

36. (new) A Schottky barrier MOSFET with an adjustable, especially negative Schottky barrier as the source or drain contact of an electronic component according to claim 35.

37. (new) A Schottky barrier MOSFET according to claim 36 wherein the contact has a silicon thickness smaller than 30 nm on an ultra thin SOI substrate.

38. (new) A MOSFET with a gate contact adjusted by means of passivation as an electronic component according to claim 35.

39. (new) A spin transistor as the electronic component according to claim 35 wherein a semiconductor silicide is selected as the metal silicide with Mn or Fe or Co doping for the formation of magnetic source and drain contacts.

40. (new) The method defined in claim 24 wherein the substrate includes Si-Ge-C, Si-C, or Si-Ge.